

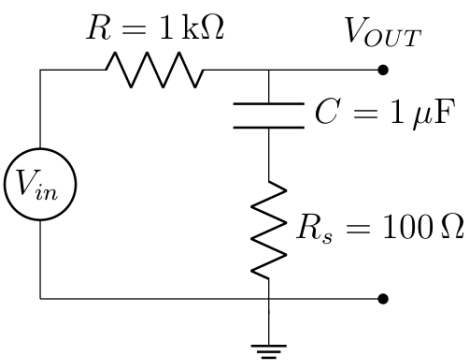
# EE3113 Homework Assignment-1

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EE18BTECH11014

**Note:** Mathematical Explanations for some of the questions are at the end.

## 1 Spice Analysis



### 1.1 1a

When  $V_{in}$  is a DC Source, Capacitor charges exponentially and at infinite time Voltage across Capacitor is  $V_{in}$ . Solving using Kirchhoff's Law and by Assuming initial charge on Capacitor is Zero and  $V_{in} = 2.5$  Volts.

$$I(t) = \frac{V_{in}}{R + R_s} e^{\frac{-t}{(R+R_s)C}} \tag{1}$$

$$V_{out} = V_{in} - \frac{V_{in}R}{R + R_s} e^{\frac{-t}{(R+R_s)C}} \tag{2}$$

#### SPICE Netlist:

```
1 Question-1a
2
3 * Circuit
4 Vin      Vin      0      DC      2.5
5 R        Vin      Vout    1k
6 C        Vout     1       1u
7 Rs       1        0       100
8
9 * Analysis
10 .op
11
12 * Results
13 .control
14 run
15 print all
16 .endc
17
18 .end
```

The results on Simulation are

$$V_{out} = 2.5 \text{ Volts} \tag{3}$$

1.2 1b

$V_{in} = \sin(\omega_0 t)$  where  $\omega_0 = 2\pi \times 100 \text{ rad/sec}$  and  $\omega_0 = 2\pi \times 1M \text{ rad/sec}$ .  $V_{out}$  varies with  $\omega_0$ .

$$\frac{V_{out}}{V_{in}} = \frac{R_s C j \omega_0 + 1}{C(R_s + R)j\omega_0 + 1} \tag{4}$$

$$V_{out} = \sqrt{\left(\frac{1 + (CR_s\omega_0)^2}{1 + (C\omega_0(R + R_s))^2}\right)} \sin\left(\omega_0 t + \tan^{-1}(R_s C \omega_0) - \tan^{-1}((R_s + R)C\omega_0)\right). \tag{5}$$

1.2.1 For  $\omega_0 = 2\pi \times 100 \text{ rad/sec}$

SPICE Netlist:

```
1 Question-1b_1
2
3 * Circuit
4 Vin      Vin      0      AC      1      SIN      0      1      100
5 R        Vin      Vout    1k
6 C        Vout     1      1u
7 Rs       1        0      100
8
9 * Analysis
10 .tran 1u 0.05
11
12 * Results
13 .control
14 run
15 plot Vin Vout
16 .endc
17
18 .end
```

Graph:

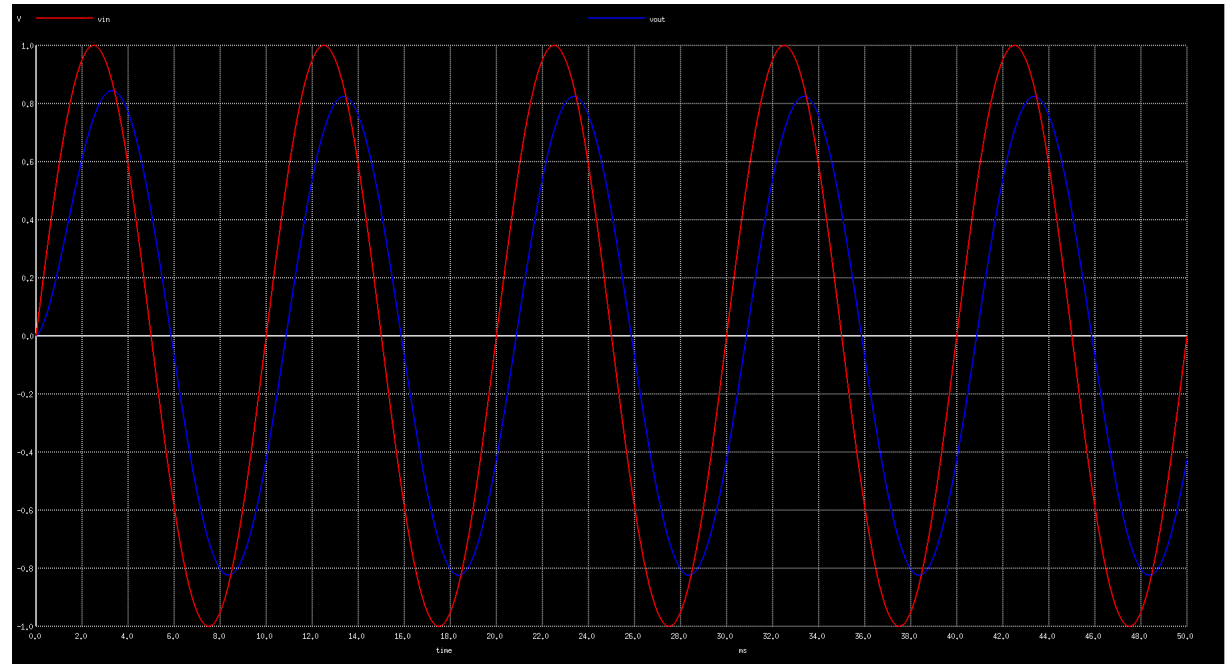


Figure 1:  $V_{out}$  and  $V_{in}$  for  $\omega = 2\pi \times 100rad/sec$

Phase Lag at  $\omega = 200\pi \times rad/sec$  is  $-31.05^\circ$ .

1.2.2 For  $\omega_0 = 2\pi \times 1M$  rad/sec

```
1 Question-1b_2
2
3 * Circuit
4 Vin      Vin      0      AC      1      SIN      0      1      1MEG
5 R        Vin      Vout    1k
6 C        Vout     1      1u
7 Rs       1        0      100
8
9 * Analysis
10 .tran 0.01n 5u
11
12 * Results
13 .control
14 run
15 plot Vin Vout
16 .endc
17
18 .end
```

Graph:

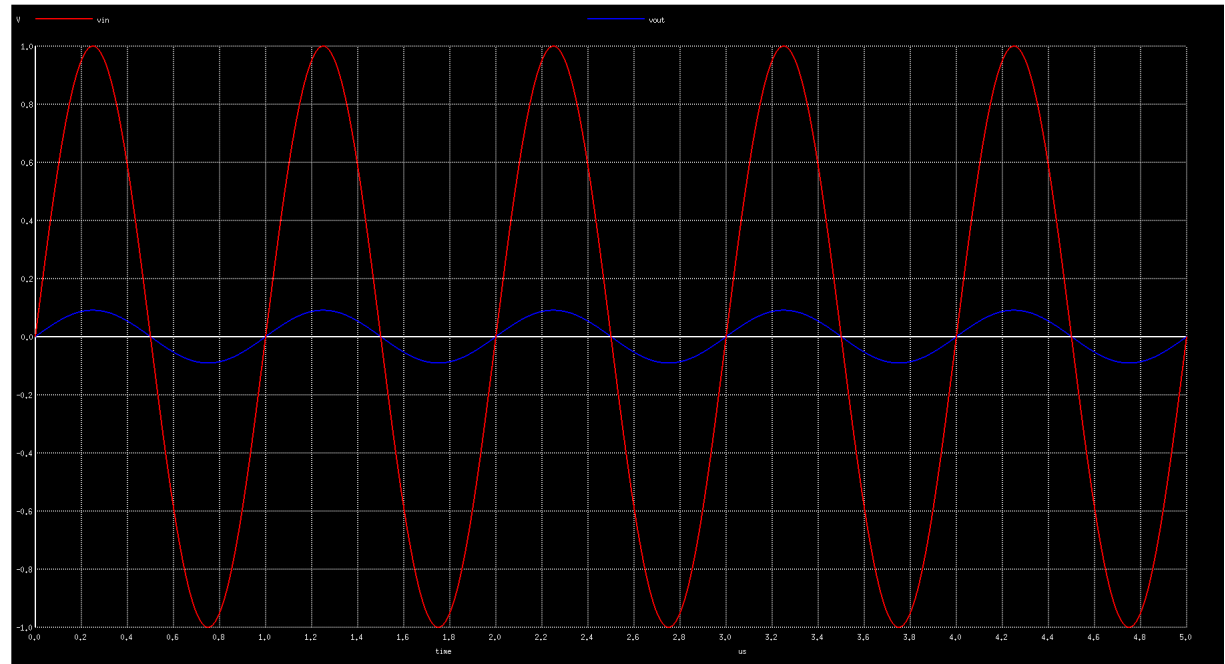


Figure 2:  $V_{out}$  and  $V_{in}$  for  $\omega = 2\pi \times 1M$  rad/sec

Phase Lag at  $\omega = 2\pi \times 10^6 rad/sec$  is  $-0.9^\circ \approx 0^\circ$ .

These values can be verified by Phase - Transfer Characteristic in next sub-section.

1.3 1c

For  $V_{in} = \sin(\omega_0 t)$ ,

$$\frac{V_{out}}{V_{in}} = \frac{R_s C j \omega_0 + 1}{C(R_s + R)j\omega_0 + 1} \tag{6}$$

$$\left\| \frac{V_{out}}{V_{in}} \right\| = \sqrt{\left( \frac{1 + (C R_s \omega_0)^2}{1 + (C \omega_0 (R + R_s))^2} \right)} \tag{7}$$

$$\angle \frac{V_{out}}{V_{in}} = \tan^{-1}(R_s C \omega_0) - \tan^{-1}((R_s + R)C \omega_0) \tag{8}$$

At 3dB point,  $\frac{V_{out}}{V_{in}} = \frac{1}{\sqrt{2}}$ . Frequency at 3dB point is  $145.89Hz$  and corresponding Phase is  $-40^\circ$ .

SPICE Netlist:

```
1 Question-1c
2
3 * Circuit
4 Vin      Vin      0      AC      1      SIN      0      1      1000
5 R        Vin      Vout    1k
6 C        Vout     1      1u
7 Rs       1        0      100
8
9 * Analysis
10 .AC      DEC      10      1      1MEG
11
12 * Results
13 .control
14 run
15 plot db(Vout/Vin)
16 plot 180*(phase(Vout) - phase(Vin))/PI
17 .endc
18
19 .end
```

Graph of Magnitude:

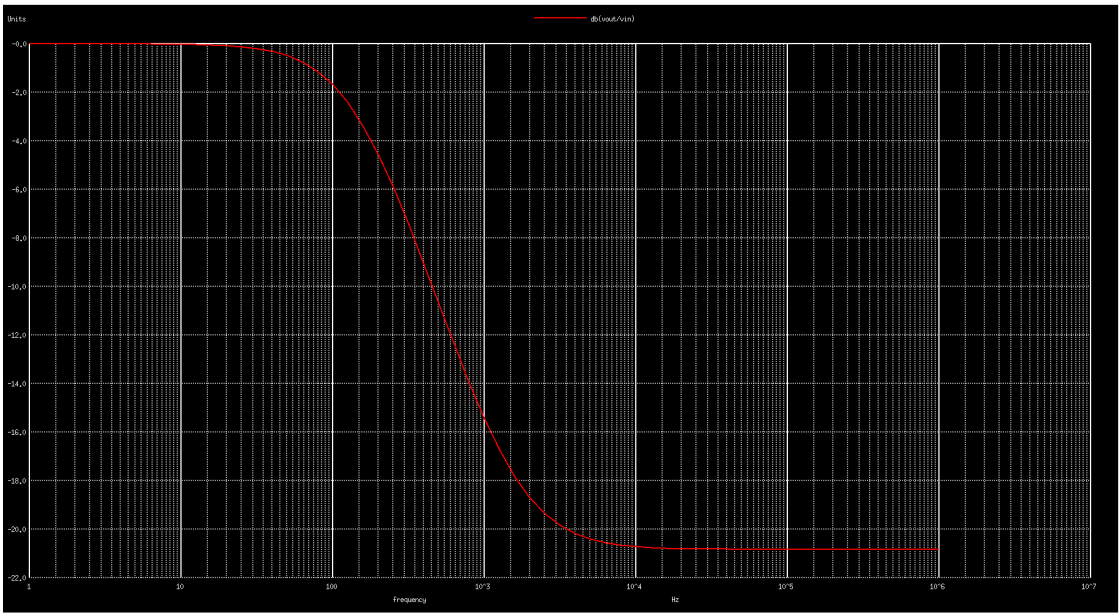


Figure 3:  $\left\| \frac{V_{out}}{V_{in}} \right\|$

Graph of Phase:

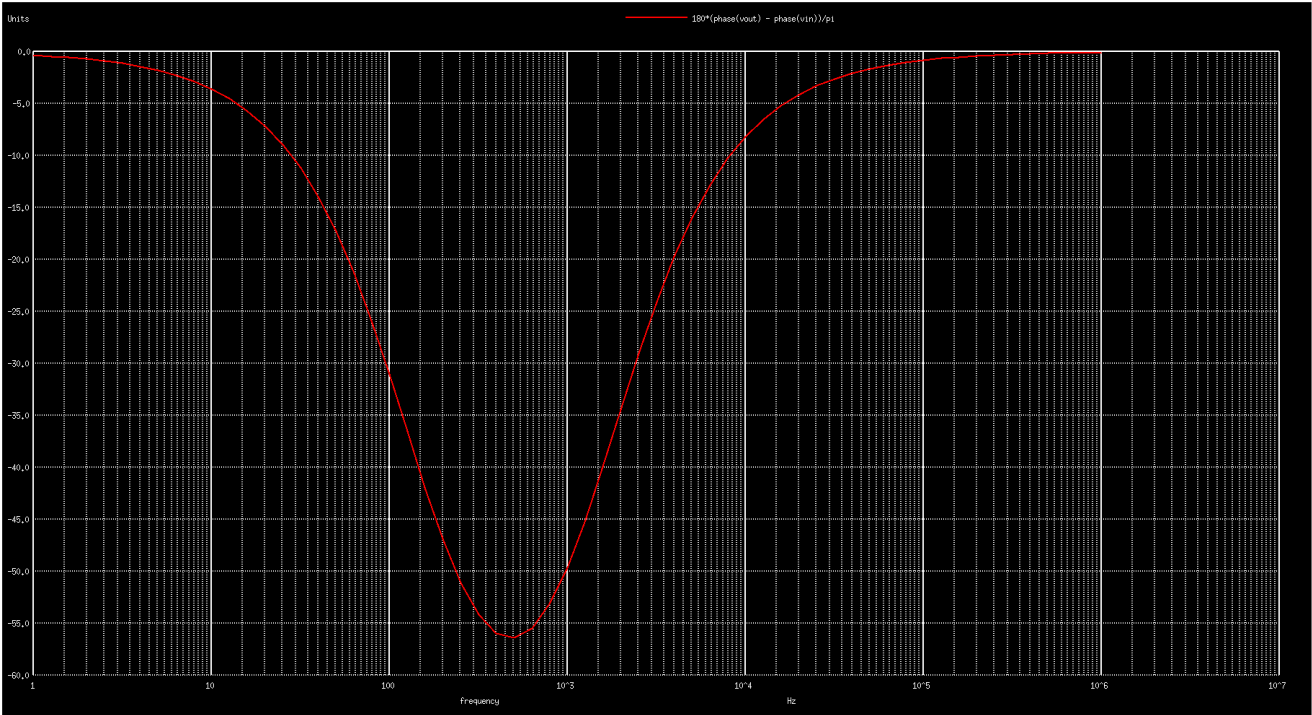


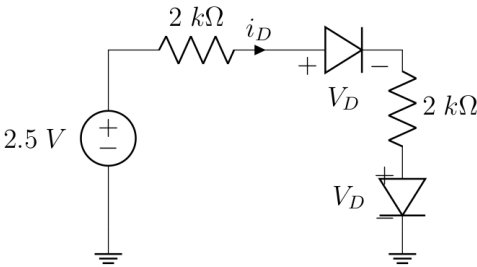
Figure 4:  $\angle \frac{V_{out}}{V_{in}}$

## 2 Analytic calculations vs SPICE simulations

$I_s = 10^{-14} \text{ Amps}$  and  $T = 300 \text{ K}$  are standard conditions for a Ideal Diode. If we consider that  $V_{Don} = 0.7 \text{ V}$  for both Diodes, Current  $i_D$  would be,

$$2.5 - 4 \times 10^3 i_D = 0.7 \times 2 \tag{9}$$

$$i_D = \frac{1.1}{4000} = 2.75 \times 10^{-4} \text{ Amps} \tag{10}$$



### 2.1 2c

SPICE Netlist:

```

1 Question-2c
2
3 * Circuit
4 V      Vin    0      DC      2.5
5 R1     Vin    1      2k
6 D1     1      Vout   CustomDiode
7 R2     Vout   2      2k
8 D2     2      0      CustomDiode
9

```

```
10 * Model
11 .model CustomDiode D
12
13 * Analysis
14 .op
15
16 * Results
17 .control
18 let ID = -Vin#branch
19 run
20 print all
21 .endc
22
23 .end
```

The results on Simulation are

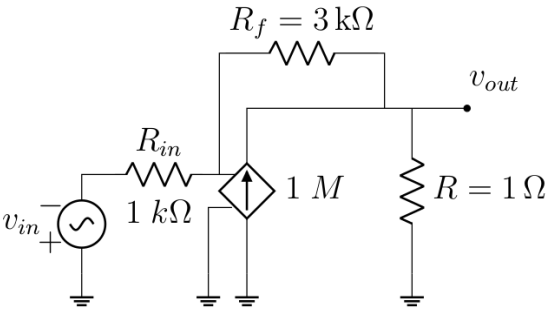
$$V_D = 0.6250153 \text{ Volts}$$

(11)

$$i_D = 3.12492 \times 10^{-4} \text{ Amps}$$

(12)

3 Controlled Sources



From the given properties,

$$V_{in} = 0.5 \sin(2000\pi t)$$

(13)

And on solving using KCL and KVL and some valid approximations,

$$V_{out} = 3V_{in}$$

(14)

$$V_{out} = 1.5 \sin(2000\pi t)$$

(15)

SPICE Netlist:

```
1 Question-3
2
3 * Circuit
4 Vin      0      1      AC      1      SIN      0      0.5      1k
5 Rin      1      2      1k
6 Rf       2      Vout    3k
7 R        Vout    0      1
8 G        Vout    0      2      0      1MEG
9
10 * Analysis
11 .tran 1u 0.005
```

```
12 *.AC DEC 10 10 10MEG
13
14 * Results
15 .control
16 run
17 plot -V(1) V(Vout)
18 *plot -V(Vout)/V(1)
19 .endc
20
21 .end
```

Graph:

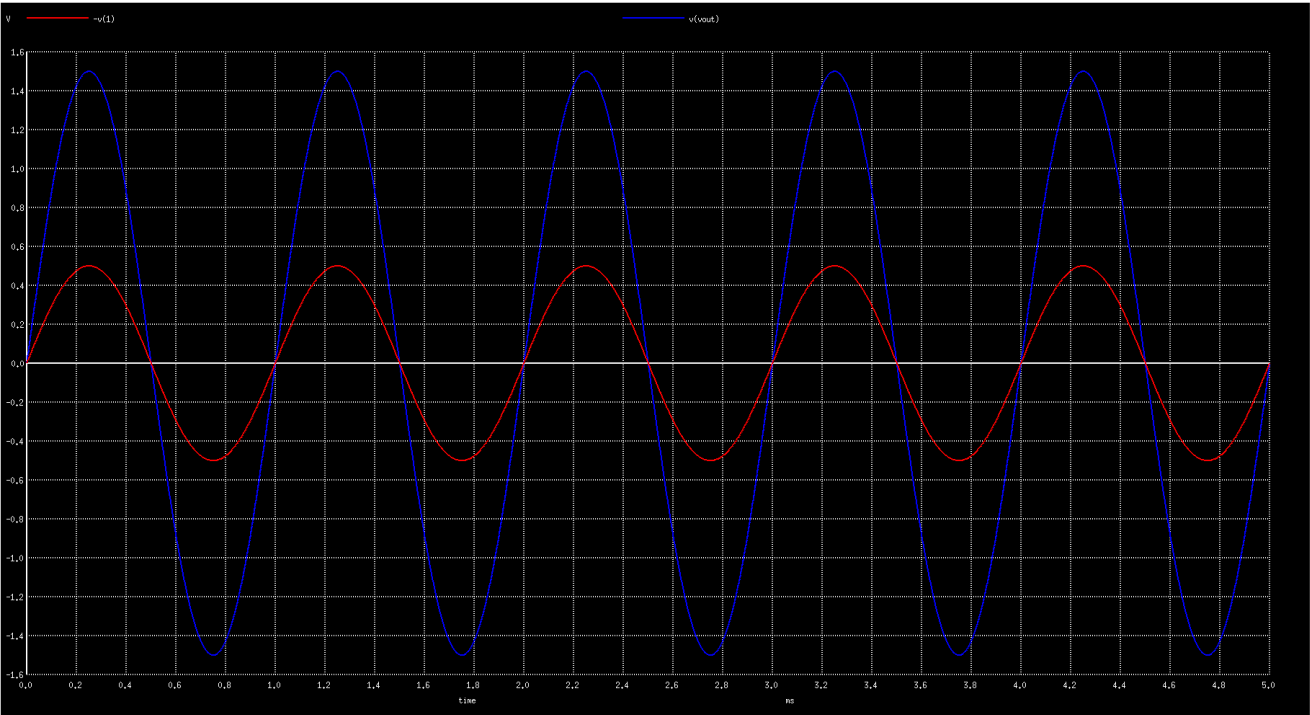


Figure 5: Plot of  $V_{out}$  and  $V_{in}$

## 4 MOSFET Characteristics

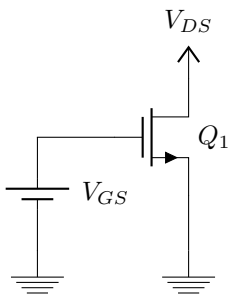
**Long Channel MOSFET Parameters and Assumptions:**

1.  $\frac{W}{L} = 1.5$
2.  $L = 10\mu m$
3.  $W = 15\mu m$
4.  $V_{GS}$  and  $V_{DS}$  are supplied +ve.

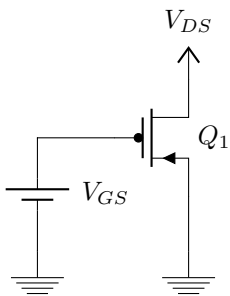
**Short Channel MOSFET Parameters and Assumptions:**

1.  $\frac{W}{L} = 1.5$
2.  $L = 0.18\mu m$
3.  $W = 0.27\mu m$
4.  $V_{GS}$  and  $V_{DS}$  are supplied -ve.

**N-MOS Circuit:**



P-MOS Circuit:



## 4.1 4a

### 4.1.1 N-MOSFET

#### Long Channel SPICE Netlist:

```

1 Question-4anmos1
2 * Vgs value varies from 0.5,2 with a step of 0.5 *
3
4 * Circuit
5 M      td      tg      0      0      nch_tt W = 15u L = 10u
6 Vgs    tg      0      DC      0.5
7 Vds    td      0      DC      0.5
8
9 * Model
10 .include "TSMC180.lib"
11 .model nch_tt nmos
12
13 * Analysis
14 .dc Vds 0 1.8 1m
15
16 * Results
17 .control
18 run
19 let ID = -Vds#branch
20 wrdata ../Data/4a/nmos11.dat      V(td)  ID
21 plot ID vs V(td)
22 .endc
23
24 .end

```

#### Short Channel SPICE Netlist:

```

1 Question-4anmos
2 * Vgs value varies from 0.5,2 with a step of 0.5 *

```



```

3
4 * Circuit
5 M      td      tg      0      0      nch_tt W = 0.27u L = 0.18u
6 Vgs    tg      0      DC      0.5
7 Vds    td      0      DC      0.5
8
9 * Model
10 .include "TSMC180.lib"
11 .model nch_tt nmos
12
13 * Analysis
14 .dc Vds 0 1.8 1m
15
16 * Results
17 .control
18 run
19 let ID = -Vds#branch
20 wrdata ../Data/4a/nmos1.dat V(td) ID
21 plot ID vs V(td)
22 .endc
23
24 .end

```

#### 4.1.2 P-MOSFET

##### Long Channel SPICE Netlist:

```

1 Question-4apmos1
2 * Vgs value varies from -2,-0.5 with a step of 0.5 *
3
4 * Circuit
5 M      td      tg      0      0      pch_tt W = 15u L = 10u
6 Vgs    tg      0      DC      -0.5
7 Vds    td      0      DC      -0.5
8
9 * Model
10 .include "TSMC180.lib"
11 .model pch_tt pmos
12
13 * Analysis
14 .dc Vds -1.8 0 1m
15
16 * Results
17 .control
18 run
19 let ID = -Vds#branch
20 wrdata ../Data/4a/pmos11.dat      V(td)  ID
21 plot ID vs V(td)
22 .endc
23
24 .end

```

##### Short Channel SPICE Netlist:

```

1 Question-4apmos
2 * Vgs value varies from -2,-0.5 with a step of 0.5 *
3
4 * Circuit
5 M      td      tg      0      0      pch_tt W = 0.27u L = 0.18u

```

```

6 Vgs      tg      0      DC      -0.5
7 Vds      td      0      DC      -0.5
8
9 * Model
10 .include "TSMC180.lib"
11 .model pch_tt pmos
12
13 * Analysis
14 .dc Vds -1.8 0 1m
15
16 * Results
17 .control
18 run
19 let ID = -Vds#branch
20 wrdata ../Data/4a/pmos1.dat      V(td)  ID
21 plot ID vs V(td)
22 .endc
23
24 .end

```

### 4.1.3 Results

#### Python Code for Plotting Characteristics from Saved Data

```

1 #Python Code to Plot Simulation from Data
2
3 import numpy as np
4 import matplotlib.pyplot as plt
5
6 def File2Numpy(Path):
7     Content = []
8     for i in open(Path).readlines():
9         Content.append(i.strip().split())
10
11     Content = np.array(Content).astype(float)
12     x = Content[:,1]
13     y = Content[:,3]
14     return np.array([x,y]).T
15
16 # Data of Long Channel N-MOSFET
17 ln1 = File2Numpy("../Data/4a/nmos11.dat")
18 ln2 = File2Numpy("../Data/4a/nmos12.dat")
19 ln3 = File2Numpy("../Data/4a/nmos13.dat")
20 ln4 = File2Numpy("../Data/4a/nmos14.dat")
21
22 # Data of Long Channel P-MOSFET
23 lp1 = File2Numpy("../Data/4a/pmos11.dat")
24 lp2 = File2Numpy("../Data/4a/pmos12.dat")
25 lp3 = File2Numpy("../Data/4a/pmos13.dat")
26 lp4 = File2Numpy("../Data/4a/pmos14.dat")
27
28 # Data of Short Channel N-MOSFET
29 sn1 = File2Numpy("../Data/4a/nmos11.dat")
30 sn2 = File2Numpy("../Data/4a/nmos12.dat")
31 sn3 = File2Numpy("../Data/4a/nmos13.dat")
32 sn4 = File2Numpy("../Data/4a/nmos14.dat")
33
34 # Data of Short Channel P-MOSFET

```

```

35 sp1 = File2Numpy("../Data/4a/pmoss1.dat")
36 sp2 = File2Numpy("../Data/4a/pmoss2.dat")
37 sp3 = File2Numpy("../Data/4a/pmoss3.dat")
38 sp4 = File2Numpy("../Data/4a/pmoss4.dat")
39
40
41 plt.figure(figsize=(20,20))
42
43 plt.subplot(2,2,1)
44 plt.plot(ln1[:,0],ln1[:,1],label=r"$V_{g}$ = 0.5")
45 plt.plot(ln2[:,0],ln2[:,1],label=r"$V_{g}$ = 1")
46 plt.plot(ln3[:,0],ln3[:,1],label=r"$V_{g}$ = 1.5")
47 plt.plot(ln4[:,0],ln4[:,1],label=r"$V_{g}$ = 2")
48 plt.title("Long Channel NMOS")
49 plt.grid()
50 plt.legend()
51 plt.xlabel(r"$V_{D}$")
52 plt.ylabel(r"$I_{D}$")
53
54 plt.subplot(2,2,2)
55 plt.plot(lp1[:,0],lp1[:,1],label=r"$V_{g}$ = -0.5")
56 plt.plot(lp2[:,0],lp2[:,1],label=r"$V_{g}$ = -1")
57 plt.plot(lp3[:,0],lp3[:,1],label=r"$V_{g}$ = -1.5")
58 plt.plot(lp4[:,0],lp4[:,1],label=r"$V_{g}$ = -2")
59 plt.title("Long Channel PMOS")
60 plt.grid()
61 plt.legend()
62 plt.xlabel(r"$V_{D}$")
63 plt.ylabel(r"$I_{D}$")
64
65 plt.subplot(2,2,3)
66 plt.plot(sn1[:,0],sn1[:,1],label=r"$V_{g}$ = 0.5")
67 plt.plot(sn2[:,0],sn2[:,1],label=r"$V_{g}$ = 1")
68 plt.plot(sn3[:,0],sn3[:,1],label=r"$V_{g}$ = 1.5")
69 plt.plot(sn4[:,0],sn4[:,1],label=r"$V_{g}$ = 2")
70 plt.title("Short Channel NMOS")
71 plt.grid()
72 plt.legend()
73 plt.xlabel(r"$V_{D}$")
74 plt.ylabel(r"$I_{D}$")
75
76 plt.subplot(2,2,4)
77 plt.plot(sp1[:,0],sp1[:,1],label=r"$V_{g}$ = -0.5")
78 plt.plot(sp2[:,0],sp2[:,1],label=r"$V_{g}$ = -1")
79 plt.plot(sp3[:,0],sp3[:,1],label=r"$V_{g}$ = -1.5")
80 plt.plot(sp4[:,0],sp4[:,1],label=r"$V_{g}$ = -2")
81 plt.title("Short Channel PMOS")
82 plt.grid()
83 plt.legend()
84 plt.xlabel(r"$V_{D}$")
85 plt.ylabel(r"$I_{D}$")
86
87 plt.savefig("4a.png")
88 plt.show()

```

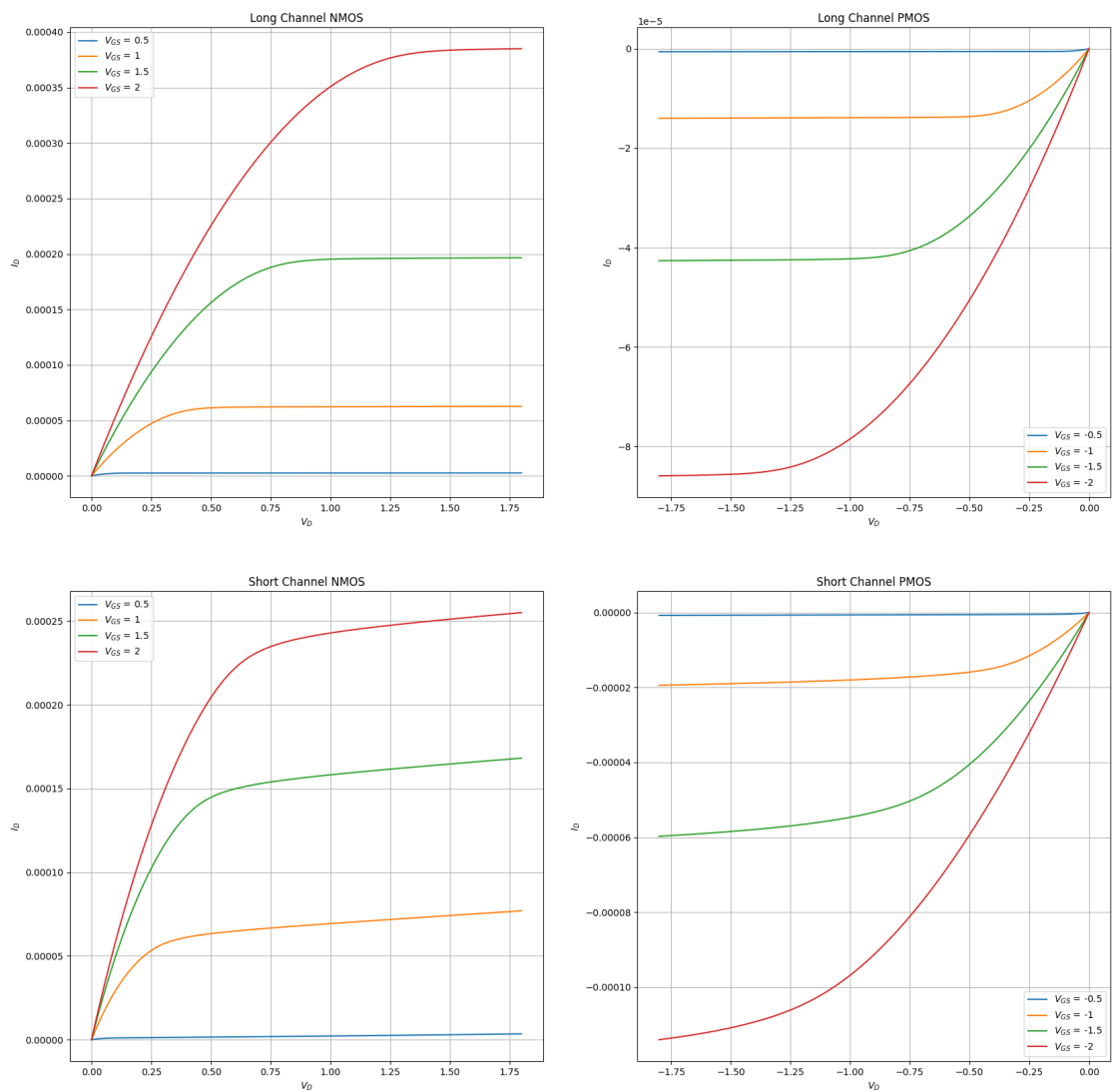


Figure 6:  $I_D$  vs  $V_D$  Characteristics of Long and Short Channel N-MOSFETs and P-MOSFETs

## 4.2 4b

### 4.2.1 N-MOSFET

#### Long Channel SPICE Netlist:

```

1 Question-4bnmos1
2
3 * Circuit
4 M      td      tg      0      0      nch_tt W = 15u L = 10u
5 Vgs    tg      0      DC      0.5
6 Vdd    td      0      DC      1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model nch_tt nmos
11
12 * Analysis
13 .dc Vgs 0 2 1m
14

```

```

15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4b/nmos1.dat V(tg)-0.362 ID
20 plot ID vs V(tg)-0.362
21 .endc
22
23 .end

```

### Short Channel SPICE Netlist:

```

1 Question-4bnmoss
2
3 * Circuit
4 M      td      tg      0      0      nch_tt W = 0.27u L = 0.18u
5 Vgs     tg      0      DC      0.5
6 Vdd     td      0      DC      1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model nch_tt nmos
11
12 * Analysis
13 .dc Vgs 0 2 1m
14
15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4b/nmoss.dat V(tg)-0.362 ID
20 plot ID vs V(tg)-0.362
21 .endc
22
23 .end

```

## 4.2.2 P-MOSFET

### Long Channel SPICE Netlist:

```

1 Question-4apmos1
2
3 * Circuit
4 M      td      tg      0      0      pch_tt W = 15u L = 10u
5 Vgs     tg      0      DC      -0.5
6 Vdd     td      0      DC      -1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model pch_tt pmos
11
12 * Analysis
13 .dc Vgs -2 0 1m
14
15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4b/pmos1.dat V(tg)-0.388 ID

```

```

20 plot ID vs V(tg)-0.388
21 .endc
22
23 .end

```

### Short Channel SPICE Netlist:

```

1 Question-4apmoss
2
3 * Circuit
4 M      td      tg      0      0      pch_tt W = 0.27u L = 0.18u
5 Vgs    tg      0      DC      -0.5
6 Vdd    td      0      DC      -1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model pch_tt pmos
11
12 * Analysis
13 .dc Vgs -2 0 1m
14
15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4b/pmoss.dat V(tg)-0.388 ID
20 plot ID vs V(tg)-0.388
21 .endc
22
23 .end

```

## 4.2.3 Results

### Python Code for Plotting Characteristics from Saved Data

```

1 #Python Code to Plot Simulation from Data
2
3 import numpy as np
4 import matplotlib.pyplot as plt
5
6 def File2Numpy(Path):
7     Content = []
8     for i in open(Path).readlines():
9         Content.append(i.strip().split())
10
11     Content = np.array(Content).astype(float)
12     x = Content[:,1]
13     y = Content[:,3]
14     return np.array([x,y]).T
15
16 # Data of Long Channel N-MOSFET
17 ln1 = File2Numpy("../Data/4a/nmos11.dat")
18 ln2 = File2Numpy("../Data/4a/nmos12.dat")
19 ln3 = File2Numpy("../Data/4a/nmos13.dat")
20 ln4 = File2Numpy("../Data/4a/nmos14.dat")
21
22 # Data of Long Channel P-MOSFET
23 lp1 = File2Numpy("../Data/4a/pmos11.dat")
24 lp2 = File2Numpy("../Data/4a/pmos12.dat")

```

```

25 lp3 = File2Numpy("../Data/4a/pmosl3.dat")
26 lp4 = File2Numpy("../Data/4a/pmosl4.dat")
27
28 # Data of Short Channel N-MOSFET
29 sn1 = File2Numpy("../Data/4a/nmoss1.dat")
30 sn2 = File2Numpy("../Data/4a/nmoss2.dat")
31 sn3 = File2Numpy("../Data/4a/nmoss3.dat")
32 sn4 = File2Numpy("../Data/4a/nmoss4.dat")
33
34 # Data of Short Channel P-MOSFET
35 sp1 = File2Numpy("../Data/4a/pmoss1.dat")
36 sp2 = File2Numpy("../Data/4a/pmoss2.dat")
37 sp3 = File2Numpy("../Data/4a/pmoss3.dat")
38 sp4 = File2Numpy("../Data/4a/pmoss4.dat")
39
40 # Transition
41 a = File2Numpy("../Data/4b/nmosl.dat")
42 b = File2Numpy("../Data/4b/pmosl.dat")
43 c = File2Numpy("../Data/4b/nmoss.dat")
44 d = File2Numpy("../Data/4b/pmoss.dat")
45
46 plt.figure(figsize=(20,20))
47
48 plt.subplot(2,2,1)
49 plt.plot(ln1[:,0],ln1[:,1],label=r"$V_{g}$ = 0.5")
50 plt.plot(ln2[:,0],ln2[:,1],label=r"$V_{g}$ = 1")
51 plt.plot(ln3[:,0],ln3[:,1],label=r"$V_{g}$ = 1.5")
52 plt.plot(ln4[:,0],ln4[:,1],label=r"$V_{g}$ = 2")
53 plt.plot(a[:,0],a[:,1],label=r"Transition")
54 plt.title("Long Channel NMOS")
55 plt.grid()
56 plt.legend()
57 plt.xlabel(r"$V_{D}$")
58 plt.ylabel(r"$I_{D}$")
59
60 plt.subplot(2,2,2)
61 plt.plot(lp1[:,0],lp1[:,1],label=r"$V_{g}$ = -0.5")
62 plt.plot(lp2[:,0],lp2[:,1],label=r"$V_{g}$ = -1")
63 plt.plot(lp3[:,0],lp3[:,1],label=r"$V_{g}$ = -1.5")
64 plt.plot(lp4[:,0],lp4[:,1],label=r"$V_{g}$ = -2")
65 plt.plot(b[:,0],b[:,1],label=r"Transition")
66 plt.title("Long Channel PMOS")
67 plt.grid()
68 plt.legend()
69 plt.xlabel(r"$V_{D}$")
70 plt.ylabel(r"$I_{D}$")
71
72 plt.subplot(2,2,3)
73 plt.plot(sn1[:,0],sn1[:,1],label=r"$V_{g}$ = 0.5")
74 plt.plot(sn2[:,0],sn2[:,1],label=r"$V_{g}$ = 1")
75 plt.plot(sn3[:,0],sn3[:,1],label=r"$V_{g}$ = 1.5")
76 plt.plot(sn4[:,0],sn4[:,1],label=r"$V_{g}$ = 2")
77 plt.plot(c[:,0],c[:,1],label=r"Transition")
78 plt.title("Short Channel NMOS")
79 plt.grid()
80 plt.legend()
81 plt.xlabel(r"$V_{D}$")

```

```
82 plt.ylabel(r"$I_{D}$")
83
84 plt.subplot(2,2,4)
85 plt.plot(sp1[:,0],sp1[:,1],label=r"$V_{g}$ = -0.5")
86 plt.plot(sp2[:,0],sp2[:,1],label=r"$V_{g}$ = -1")
87 plt.plot(sp3[:,0],sp3[:,1],label=r"$V_{g}$ = -1.5")
88 plt.plot(sp4[:,0],sp4[:,1],label=r"$V_{g}$ = -2")
89 plt.plot(d[:,0],d[:,1],label=r"Transition")
90 plt.title("Short Channel PMOS")
91 plt.grid()
92 plt.legend()
93 plt.xlabel(r"$V_{D}$")
94 plt.ylabel(r"$I_{D}$")
95
96 plt.savefig("4b.png")
97 plt.show()
```

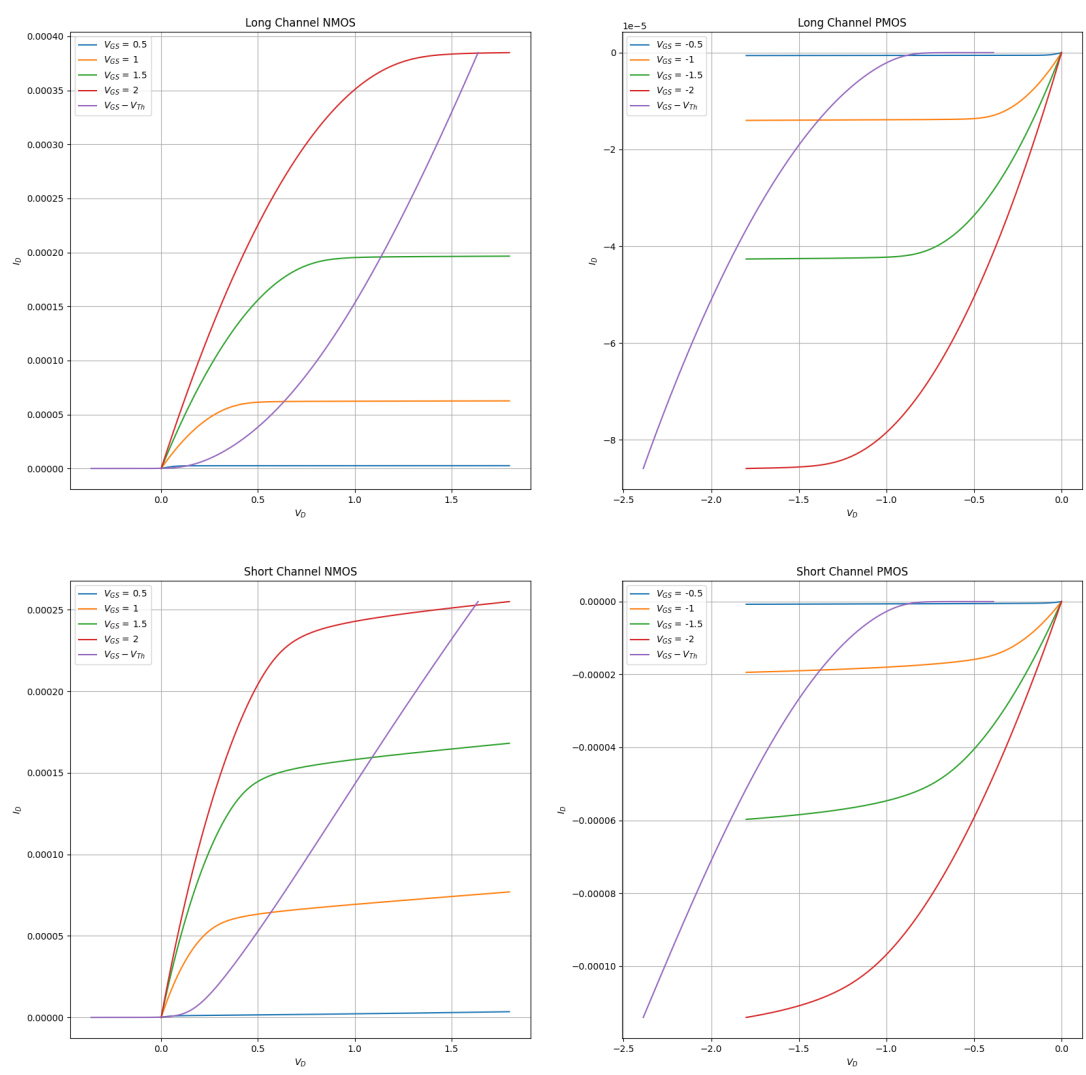


Figure 7:  $I_D$  vs  $V_D$  Characteristics of Long and Short Channel N-MOSFETs and P-MOSFETs with Regions

The Graph of  $I_D$  vs  $V_{GS} - V_{Th}$  separates Linear Region from Saturation Region. The side of Parabolic Curve where  $I_D$  vs  $V_D$  varies Linearly is the Linear Region and the other one is Saturation Region.



The Primary Difference between the Graphs in Long Channel and Short Channel MOSFETs is value of Channel Modulation Parameter  $\lambda$ .  $\lambda \approx 0$  for Long Channel Devices and  $\lambda$  is considerably large for Small Channel Devices. The considerable increase in  $\lambda$  is one of the Short Channel Effects which happens due to shortening of length of the inverted channel region with increase in drain bias for large drain biases. For  $\lambda = 0$ ,  $I_D$  vs  $V_{DS}$  graph saturates at the end whereas for considerable  $\lambda$   $I_D$  vs  $V_{DS}$  graph doesn't saturate.

### 4.3 4c

The Small Signal Output Resistance  $r_0$  parameter of the MOSFET doesn't depend on Small Signal Input Voltage. It also depends on Channel Modulation Parameter  $\lambda$ . It is independent on whether it is N-MOS or P-MOS.

$$g_o = \left. \frac{\partial i_D}{\partial v_{DS}} \right|_Q = \mu_n C_{ox} \left( \frac{W}{2L} \right) (V_{GS} - V_{Tn})^2 \lambda_n \cong \lambda I_D \quad (16)$$

$$r_o = \frac{1}{g_o} = \frac{1}{\lambda I_D} \quad (17)$$

#### 4.3.1 Calculations

Calculations are done for Graphs in Question-4a or for Section-4a in this document for  $V_{GS} = 1.5$  Volts.

$$r_0 = \frac{1}{\left( \frac{dI_D}{dV_{DS}} \right)} \quad (18)$$

$$r_0 = \frac{dV_{DS}}{dI_D} \quad (19)$$

#### N-MOSFET

Long Channel Calculations:

$$\frac{dI_D}{dV_{DS}} = 0 \quad (20)$$

$$r_0 \approx \infty \quad (21)$$

Short Channel Calculations:

$$\frac{dI_D}{dV_{DS}} = 1.17647 \times 10^{-5} \Omega^{-1} \quad (22)$$

$$r_0 = 85000 \Omega \quad (23)$$

#### P-MOSFET

Long Channel Calculations:

$$\frac{dI_D}{dV_{DS}} = 2.117 \times 10^{-8} \Omega^{-1} \quad (24)$$

$$r_0 = 4.722 \times 10^7 \Omega \quad (25)$$

Short Channel Calculations:

$$\frac{dI_D}{dV_{DS}} = 1.468 \times 10^{-7} \Omega^{-1} \quad (26)$$

$$r_0 = 6.8102 \times 10^6 \Omega \quad (27)$$

## 4.4 4d

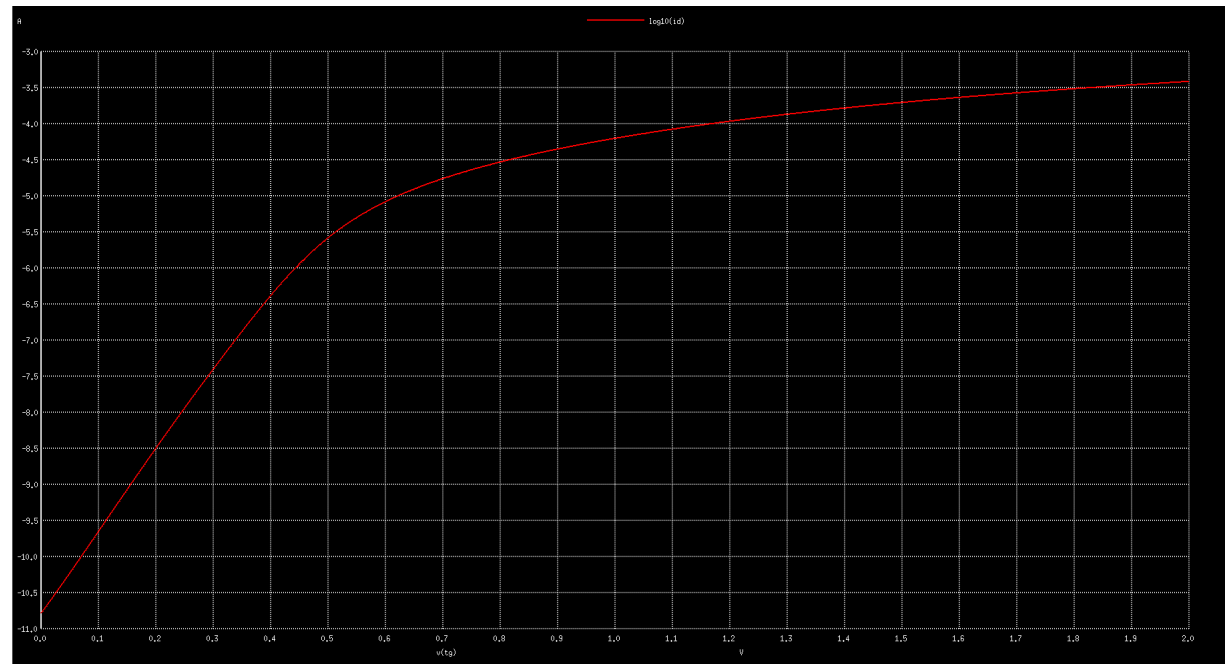
### 4.4.1 N-MOSFET

#### Long Channel

SPICE Netlist:

```
1 Question-4dnmos1
2
3 * Circuit
4 M      td      tg      0      0      nch_tt W = 15u L = 10u
5 Vgs    tg      0      DC      0.5
6 Vdd    td      0      DC      1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model nch_tt nmos
11
12 * Analysis
13 .dc Vgs 0 2 0.1m
14
15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4d/nmos1.dat V(tg) log10(ID)
20 plot log10(ID) vs V(tg)
21 .endc
22
23 .end
```

Plot:



Calculations:

$$S = 0.0921821 \text{ V/dec} \tag{28}$$

$$S = \eta \frac{KT}{q} \ln(10) \tag{29}$$

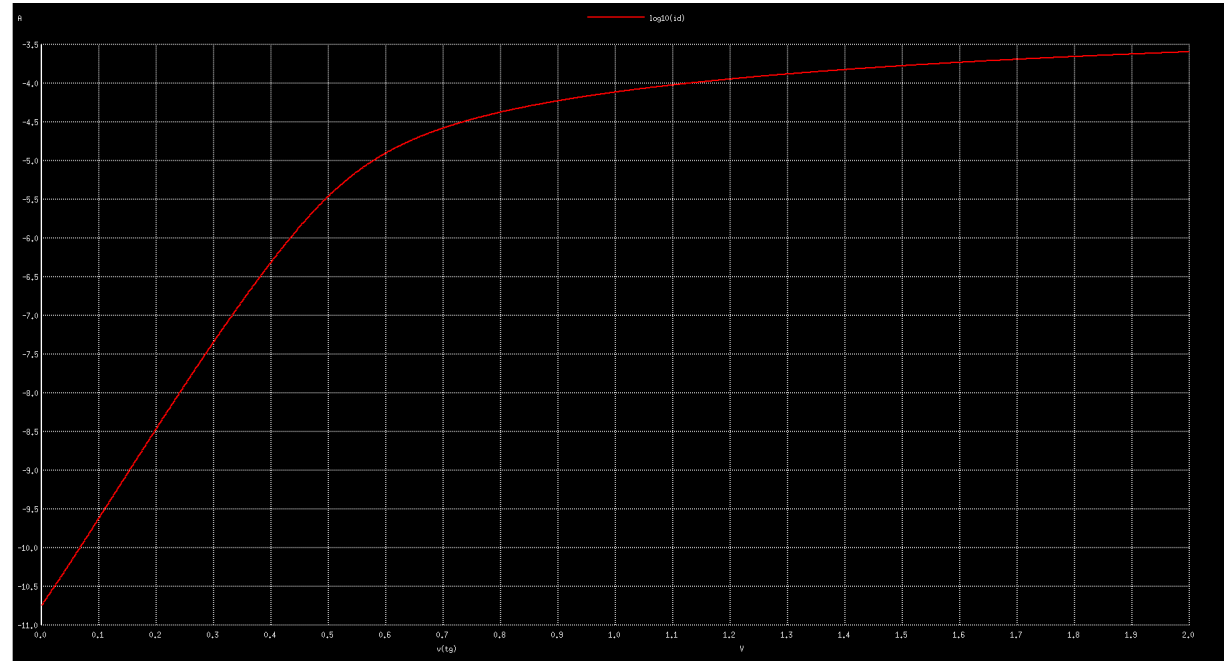
$$\eta = 1.5514 \tag{30}$$

Short Channel

SPICE Netlist:

```
1 Question-4dnmoss
2
3 * Circuit
4 M      td      tg      0      0      nch_tt W = 0.27u L = 0.18u
5 Vgs    tg      0      DC      0.5
6 Vdd    td      0      DC      1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model nch_tt nmos
11
12 * Analysis
13 .dc Vgs 0 2 1m
14
15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4d/nmoss.dat V(tg) log10(ID)
20 plot log10(ID) vs V(tg)
21 .endc
22
23 .end
```

Plot:



Calculations:

$$S = 0.0906977 \text{ V/dec} \tag{31}$$

$$S = \eta \frac{KT}{q} \ln(10) \tag{32}$$

$$\eta = 1.52645 \tag{33}$$

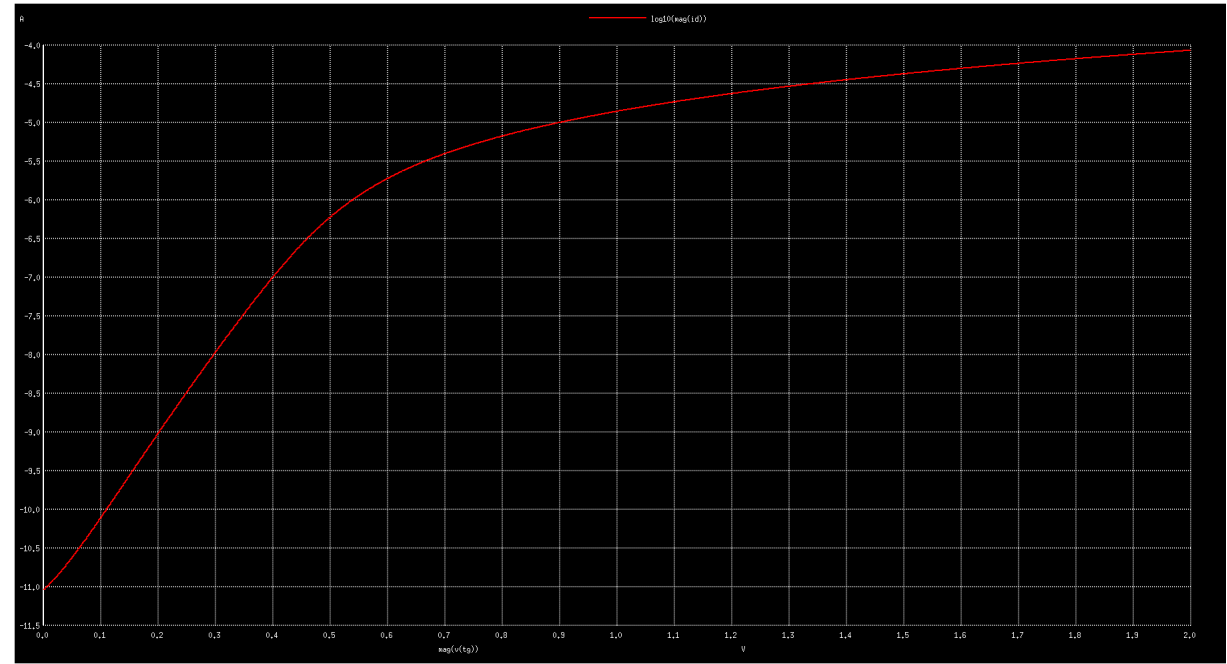
4.4.2 P-MOSFET

Long Channel

SPICE Netlist:

```
1 Question-4dpmos1
2
3 * Circuit
4 M      td      tg      0      0      pch_tt W = 15u L = 10u
5 Vgs    tg      0      DC      -0.5
6 Vdd    td      0      DC      -1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model pch_tt pmos
11
12 * Analysis
13 .dc Vgs -2 -0 1m
14
15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4d/pmos1.dat V(mag(tg))      log10(mag(ID))
20 plot log10(mag(ID)) vs mag(V(tg))
21 .endc
22
23 .end
```

Plot:



Calculations:

$S = 0.0930233 \text{ V/dec}$  (34)

$S = \eta \frac{KT}{q} \ln(10)$  (35)

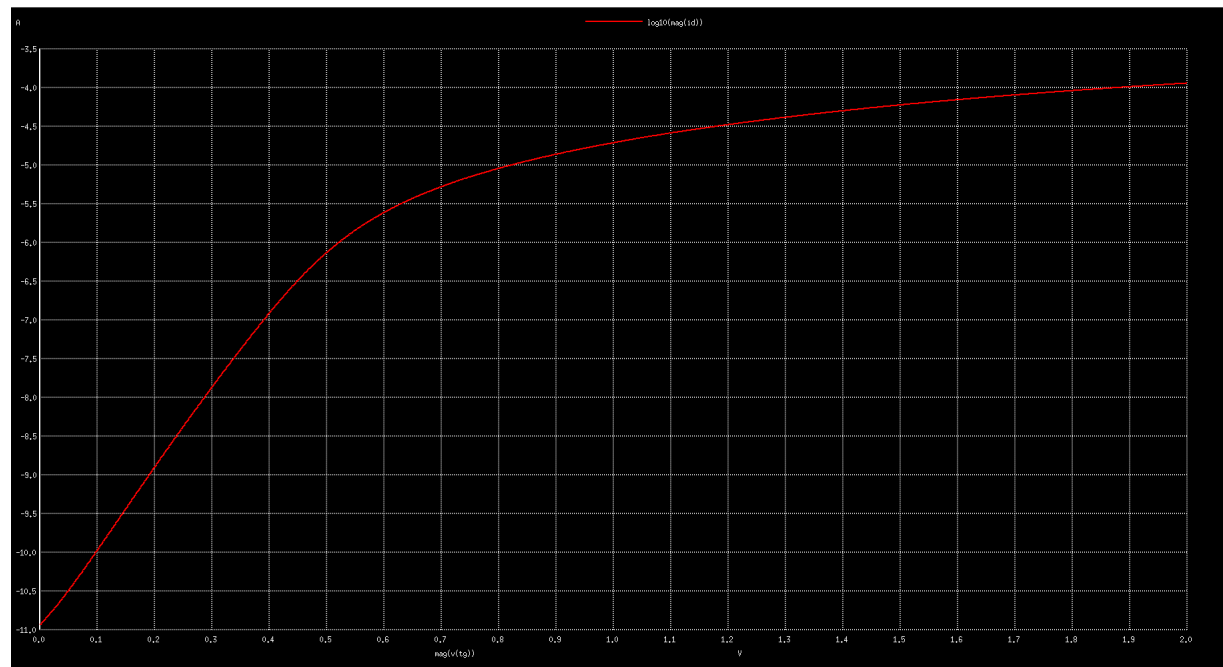
$\eta = 1.56559$  (36)

Short Channel

SPICE Netlist:

```
1 Question-4dpmoss
2
3 * Circuit
4 M      td      tg      0      0      pch_tt W = 0.27u L = 0.18u
5 Vgs    tg      0      DC      -0.5
6 Vdd    td      0      DC      -1.8
7
8 * Model
9 .include "TSMC180.lib"
10 .model pch_tt pmos
11
12 * Analysis
13 .dc Vgs -2 0 1m
14
15 * Results
16 .control
17 run
18 let ID = -Vdd#branch
19 wrdata ../Data/4d/pmos.dat mag(V(tg))      log10(mag(ID))
20 plot log10(mag(ID)) vs mag(V(tg))
21 .endc
22
23 .end
```

Plot:



Calculations:

$S = 0.0991792 \text{ V/dec}$  (37)

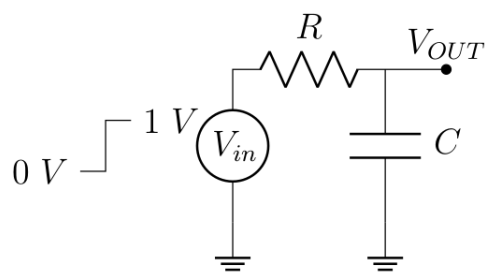
$S = \eta \frac{KT}{q} \ln(10)$  (38)

$\eta = 1.66919$  (39)

# 5 Propagation Delay

**Propagation Delay:** Propagation Delay is the difference between time taken by the Output to have its magnitude half of its Final Value and time taken for the Input to have its magnitude half of its Final Value.

**Rise Time:** Rise Time is the amount of time taken for the Signal to have its magnitude change from 10% to 90% of Steady State Value.



## 5.1 5a

When a Ideal Step Signal( $t_{r,in} = 0$ ) is given as input to the given RC Circuit,

$$V_{out} = V_{in}(1 - e^{\frac{-t}{RC}}) \tag{40}$$

$$\text{Propagation Delay} = t_p = 0.69RC \tag{41}$$

$$\text{Rise Time} = t_r = 2.2RC \tag{42}$$

Assuming,

$$R = 1000\Omega \tag{43}$$

$$C = 1\mu F \tag{44}$$

$$t_p = 6.9 \times 10^{-4}s \tag{45}$$

$$t_r = 2.2 \times 10^{-3}s \tag{46}$$

### SPICE Netlist:

```
1 **destroy all
2
3 Vin      Vin      0      AC      1      PWL(0 0V 0 1V 1 1V)
4 R        Vin      Vout    1000
5 C        Vout     0      1u
6
7 * ANALYSIS
8 .tran 1u 0.008
9
10 * VIEW RESULTS
11 .control
12 run
13 plot Vin Vout
14 .endc
15
16 .end
```

**Graph:**

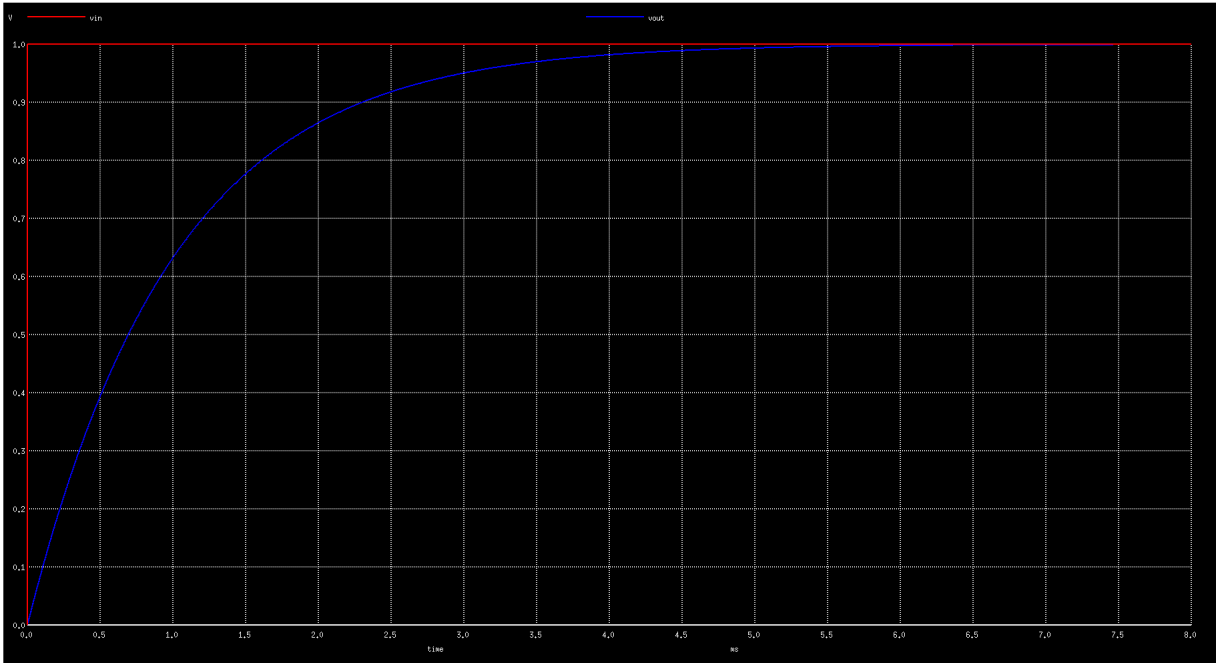


Figure 8:  $V_{out}$  and  $V_{in}$  for Ideal Step Signal as Input

5.2 5b

Parameters:

$$R = 10\Omega \tag{47}$$

$$C = 1nF \tag{48}$$

Readings: Table containing values of  $\alpha = t_{r,in}/0.8$  and corresponding  $t_{p,out}$ .

$\alpha$ (in sec)	$t_{p,out}$ (in sec)
$10 \times 10^{-12}$	$6.9434 \times 10^{-9}$
$50 \times 10^{-12}$	$6.96226 \times 10^{-9}$
$100 \times 10^{-12}$	$7 \times 10^{-9}$
$200 \times 10^{-12}$	$7.02 \times 10^{-9}$
$300 \times 10^{-12}$	$7.1 \times 10^{-9}$
$400 \times 10^{-12}$	$7.137 \times 10^{-9}$
$500 \times 10^{-12}$	$7.185 \times 10^{-9}$
$600 \times 10^{-12}$	$7.23491 \times 10^{-9}$
$700 \times 10^{-12}$	$7.28977 \times 10^{-9}$
$800 \times 10^{-12}$	$7.34026 \times 10^{-9}$
$900 \times 10^{-12}$	$7.39123 \times 10^{-9}$
$1 \times 10^{-9}$	$7.44 \times 10^{-9}$
$2 \times 10^{-9}$	$7.9 \times 10^{-9}$
$3 \times 10^{-9}$	$8.47558 \times 10^{-9}$
$4 \times 10^{-9}$	$9.00455 \times 10^{-9}$
$5 \times 10^{-9}$	$9.54167 \times 10^{-9}$
$6 \times 10^{-9}$	$1.00883 \times 10^{-8}$
$7 \times 10^{-9}$	$1.06419 \times 10^{-8}$
$8 \times 10^{-9}$	$1.12035 \times 10^{-8}$
$9 \times 10^{-9}$	$1.17738 \times 10^{-8}$
$10 \times 10^{-9}$	$1.23509 \times 10^{-8}$

$$t_p = t_{p,out} - t_{p,in} \quad (49)$$

$$t_{p,in} = \alpha/2 \quad (50)$$

### Python Code for Simulation:

```

1 import numpy as np
2 import matplotlib.pyplot as plt
3
4 alpha = np.array([10*1e-12, 50*1e-12, 100*1e-12, 200*1e-12, 300*1e-12, 400*1e-12,
5                   500*1e-12, 600*1e-12, 700*1e-12, 800*1e-12, 900*1e-12, 1*1e-9,
6                   2*1e-9, 3*1e-9, 4*1e-9, 5*1e-9, 6*1e-9, 7*1e-9, 8*1e-9, 9*1e-9, 10*1e-9])
7
8 tpout = np.array([6.9434*1e-9, 6.96226*1e-9, 7*1e-9, 7.02*1e-9, 7.1*1e-9, 7.137*1e-9,
9                   7.185*1e-9, 7.23491*1e-9, 7.28977*1e-9, 7.34026*1e-9, 7.39123*1e-9, 7.44*1e-9,
10                  7.9*1e-9, 8.47558*1e-9, 9.00455*1e-9, 9.54167*1e-9, 1.008833*1e-8, 1.06419*1e-8,
11                  1.12035*1e-8, 1.17738*1e-8, 1.23509*1e-8])
12
13 tr = 0.8*alpha
14 tpin = alpha/2
15 tp = tpout - tpin
16
17 plt.figure(figsize=(9,9))
18 plt.plot(tr,tp)
19 plt.grid()
20 plt.scatter(tr,tp)
21 plt.title(r"$t_{p}$ vs $t_{r,in}$")
22 plt.xlabel(r"$t_{r,in}$")
23 plt.ylabel(r"$t_{p}$")
24 plt.savefig("5b.png")
25 plt.show()

```

### Results:

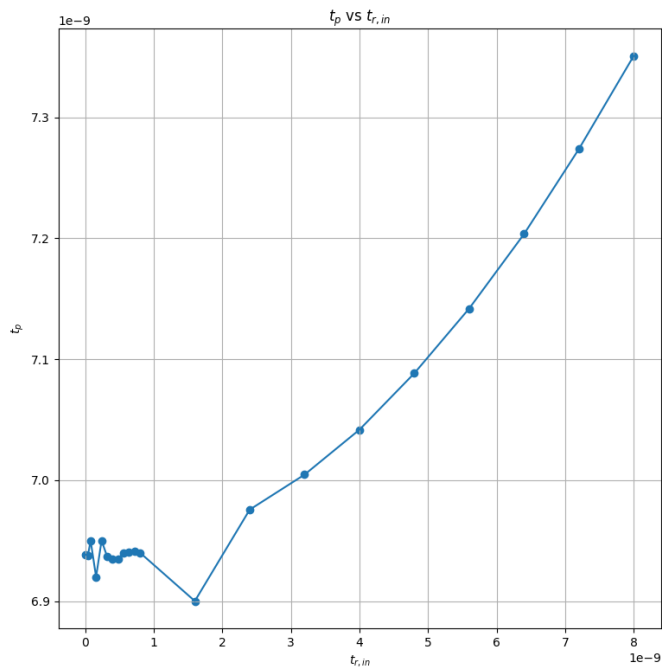


Figure 9: Plot  $t_p$  vs  $t_{r,in}$